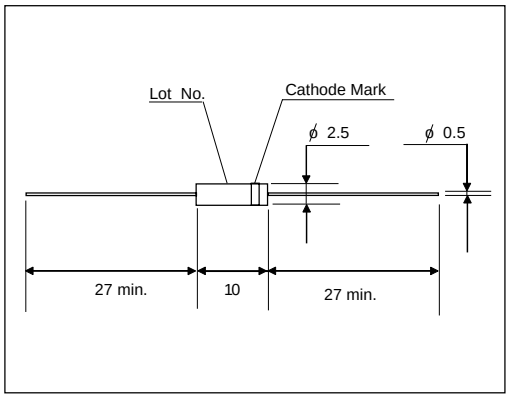
ESJA09-12 (12kV/5mA)

HIGH VOLTAGE DIODE

ESJA09 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

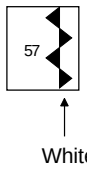
■ Outline Drawings : mm



■ Features

- High speed switching
- Low VF
- High surge resisitivity for CRT discharge
- High reliability design
- Ultra small pakage

■ Cathode Mark

Type	Mark
ESJA09-12	

■ Applications

- Rectification for CRT display monitor high voltage power supply (FBT:Flyback Transformer)

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Condition	ESJA09-12	Units
Repetitive Peak Renerse Voltage	V_{RRM}		**12**	kV
Average Output Current	I_O	Ta=25°C,Resistive Load	5	mA
Suege Current	I_{FSM}	10mS Sine-half wave peak value	0.5	A_{peak}
Junction Temperature	T_j		120	°C
Allowable Operation Case Temperature	Tc		100	°C
Storage Temperature	T_{stg}		-40 to +120	°C

● Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	ESJA09-12	Units
Maximum Forward Voltage Drop	V_F	at 25°C,I_F=10mA	42	V
Maximum Reverse Current	IR1	at 25°C,V_R=12kV	2	μA
	IR2	at 100°C,V_R=12kV	5	μA
Maximum Reverse Recovery Time	trr	at 25°C,I_F=2mA,I_R=4mA	0.05	μs
Junction Capacitance	Cj	at 25°C,V_R=0V,f=1MHz	1	pF

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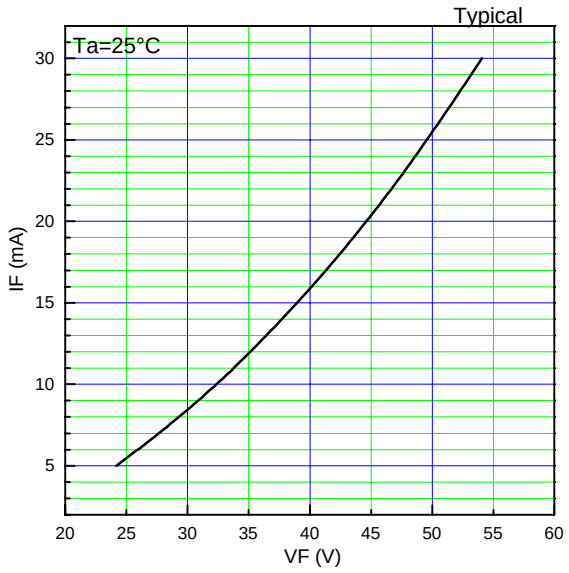
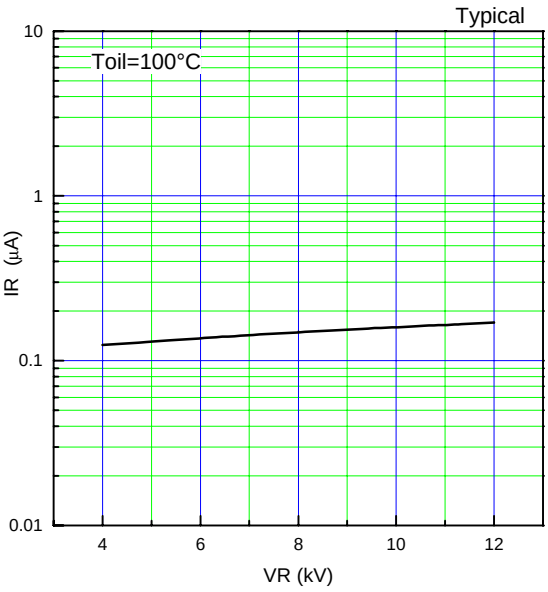
■ Characteristics

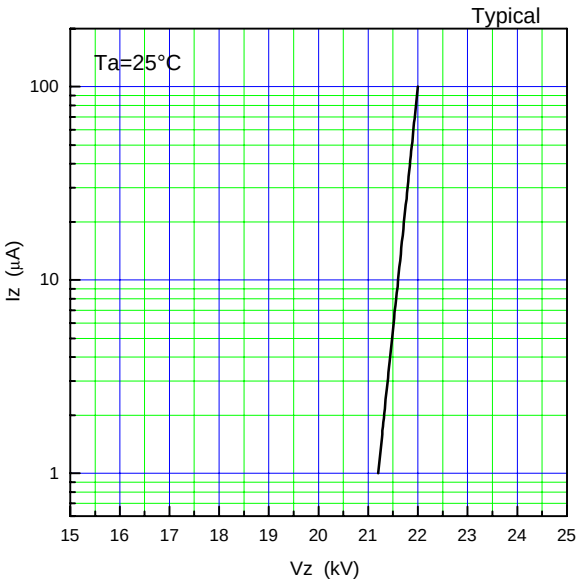
Forward characteristic (VF-IF)



Reverse characteristic (VR-IR)



Avalanche characteristic (Vz-Iz)



Reverse recovery time characteristic (Ta-trr)